# E ect of Spin-Flip Scattering on Electrical Transport in M agnetic Tunnel Junctions

Zhen-G ang Zhu, G ang Su , Q ing-R ong Zheng and B iao Jin Departm ent of Physics, The G raduate School of the Chinese A cadem y of Sciences, P.O. Box 3908, Beijing 100039, China

## Abstract

By means of the nonequilibrium G reen function technique, the e ect of spin- ip scatterings on the spin-dependent electrical transport in ferrom agnet-insulator-ferrom agnet (FM -I-FM) tunnel junctions is investigated. It is shown that Julliere<sup>0</sup>s form ula for the tunnel conductance m ust be m odi ed when including the contribution from the spin- ip scatterings. It is found that the spin- ip scatterings could lead to an angular shift of the tunnel conductance, giving rise to the junction resistance not being the largest when the orientations of m agnetizations in the two FM electrodes are antiparallel, which m ay o er an alternative explanation for such a phenom enon observed previously in experiments in som e FM -I-FM junctions. The spin- ip assisted tunneling is also observed.

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Spin-dependent electrical transport in magnetic tunnel junctions has received much attention both theoretically and experimentally in recent years (see e.g. Refs. [1] for review). A new eld dubbed as spintronics (i.e. spin-based electronics) is emerging. Among others one of the simplest devices in spintronics would be a ferrom agnet-insulator-ferrom agnet (FM -IFM) structure which is comprised of two ferrom agnetic electrodes separated by an insulator thin Im. In 1975 Julliere made the rst observation of spin-polarized electrons tunneling through an insulator lm into a ferrom agnetic metal lm, and clearly observed 14% tunnelm agnetoresistance (TMR) for Fe/Ge/Co junctions at 4.2 K [2]. In 1995, Moodera et alm ade a breakthrough that they observed over a 10% TMR for a Co/A  $\downarrow$ O  $_3$ /N  $i_{80}$  Fe<sub>20</sub> junction reproducibly at room temperature [3]. Since then, there are a variety of works toward enhancing TMR in magnetic tunnel junctions, and the TMR > 30% has been obtained at room tem perature [1]. On the other hand, to understand the spin-polarized tunneling results for FM -IFM junctions, people usually invoke the model based on a classical tunneling theory proposed by Julliere [2], in which spins of electrons during tunneling are supposed to be conserved, namely, the tunneling of spin-up and spin-down electrons are two quite independent processes, and spin- ip scatterings are neglected. Though Julliere's two-current m odel can interpret well som e experim ental results qualitatively, it still faces to di culties for more complex situations. A ctually, in some experiments spin conservation no longer holds, and the spin- ip scattering may take e ect on the transport properties. There has been a number of experiments [1,4] showing that TMR can be very various for dierent barriers, and the inverse TMR can even occur, namely, the resistance when the orientations of magnetizations of the two ferrom agnets are parallel, is larger than that of antiparallel orientations. It appears that the spin- ip scatterings might not be ignored in these situations. Recently, Vedyayev et al investigated a model including impurities in the middle of the barrier, and considered both cases of spin conserving scattering and spin- ip scattering [5]. Besides, Ja reset alm easured the angular dependence of the TMR for transition-m etal based junctions, and observed that the angular response is beyond the simple cosine shape **[6].** 

In this paper, based on a m icroscopic m odel and using the nonequilibrium G reen function technique we shall give a more general expression of the angular dependence of the TM R for FM -IFM junctions by including the e ect of spin- ip scatterings. It is found that the e ect of spin- ip scatterings gives rise to a correction to the form ula of the usual tunnel conductance. Speci cally, we have found that the spin- ip scattering induces a phase shift, leading to the tunnel conductance not to be the smallest when the magnetizations of the two FM electrodes are antiparallel, which may provide an alternative explanation for the previously experimental observation of the angular shift in som e FM -IFM tunnel junctions. In addition, it has been shown that the spin- ip scattering could also lead to the inverse TM R e ect under certain conditions though it is not the only factor, and the spin- ip assisted tunneling is also observed.

Let us consider a magnetic tunnel junction consisting of two ferrom agnetic  $\ln s$  separated by an insulator thin  $\ln A$  steady bias voltage is applied to the junction. The relative orientation of magnetizations in the two ferrom agnets is characterized by the angle . The Ham iltonian of the system reads

$$H = H_{L} + H_{R} + H_{T};$$
(1)

with

$$H_{L} = {}^{X} {}^{H_{L}} a_{k}^{Y} a_{k} ;$$

$$H_{R} = {}^{X} {}^{(I'_{R}} (q) M_{2} \cos )c_{q}^{Y} c_{q} M_{2} \sin c_{q}^{Y} c_{q}^{-}];$$

$$H_{T} = {}^{q} {}^{X} {}^{(I'_{R}} a_{k}^{0} a_{k}^{Y} c_{q}^{0} + T_{kq}^{0} c_{q}^{Y} a_{k} ];$$

where  $a_k$  and  $q_k$  are annihilation operators of electrons with momentum k and spin (= 1) in the left and right ferrom agnets, respectively,  $"_{k}^{L} = "_{L}(k) eV M_{1}; M_{1} = \frac{g_{B}h_{L}}{2};$  $M_2 = \frac{g_B h_R}{2}$ ; g is Lande factor, <sub>B</sub> is Bohr magneton,  $h_{L(R)}$  is the molecular eld of the left (right) ferrom agnet, " $_{L(R)}(k)$  is the single-particle dispersion of the left (right) FM electrode, V is the applied bias voltage,  $T_{kq}^{0}$  denotes the spin and momentum dependent tunneling am plitude through the insulating barrier. Note that the spin-ip scattering is included in H<sub>T</sub> when  $^{0}$  = = . It is this term that violates the spin conservation in the tunneling process. By perform ing the u v transform ation,  $c_q = \cos_{\overline{2}}b_q$  sin  $_{\overline{2}}b_q$ ,  $c_q^y = \cos_{\overline{2}}b_q^y$  sin  $_{\overline{2}}b_q^{-}$ ;  $H_R$  becomes  $H_R = {\stackrel{P}{}}_{q} {\stackrel{\mathbf{n}}{}_{q}} {\stackrel{R}{}_{q}} {\stackrel{b}{}_{q}} {\stackrel{with}{}_{q}} {\stackrel{\mathbf{n}}{}_{q}} {\stackrel{\mathbf{n}}{}_{q}$ has the form of

$$I_{L}(V) = e N_{L} = \frac{2e}{h} R e_{kq}^{X} Trf_{kq} G_{kq}^{(t; t)}(t; t)g; \qquad (2)$$

where  $_{kq} = T_{kq} R$  with  $T_{kq} = \begin{bmatrix} T_{kq}^{""} & T_{kq}^{""} \\ T_{kq}^{\#"} & T_{kq}^{\#"} \end{bmatrix}$  and  $R = \begin{bmatrix} \cos_{\overline{2}} & \sin_{\overline{2}} \\ \sin_{\overline{2}} & \cos_{\overline{2}} \end{bmatrix}$ ; and Tr stands for the trace of matrix taking over the spin space. The lesser G reen function,  $G_{kq}^{<}(t; t^{0})$ ; is

de ned in a steady state as

$$G_{kq}^{<}(t t^{0}) = \begin{array}{c} G_{kq}^{"",<}(t t^{0}) & G_{kq}^{\#",<}(t t^{0}) \\ G_{kq}^{"\#,<}(t t^{0}) & G_{kq}^{\#\#,<}(t t^{0}) \end{array};$$
(3)

with  $G_{kq}^{0, \prec}$  (t t<sup>0</sup>)  $ia_{k}^{y}$  (t<sup>0</sup>) $b_{q} \circ$  (t) E. To obtain the lesser G reen function, one needs to introduce a tim e-ordered G reen function G  $_{\rm gk}^{\rm t}$  as

$$G_{qk}^{t}(t t^{0}) = G_{qk}^{"",t}(t t^{0}) G_{qk}^{"\#t}(t t^{0})^{!}; \qquad (4)$$

$$G_{qk}^{\#",t}(t t^{0}) G_{qk}^{\#\#t}(t t^{0})$$

with  $G_{qk}^{0,t}$  (t t<sup>0</sup>)  $i T fb_{q}$  (t) $a_{k}^{y} \circ (t^{0})g : By using the equation of motion, we get$ 

$$G_{qk}^{t}(") = \int_{q^{0}}^{X} F_{qq^{0}}^{t}(") \int_{kq^{0}}^{Y} g_{kL}^{t}("); \qquad (5)$$

with

$$F_{qq^{0}}^{t}(") = g_{q^{0}R}^{t}(")_{qq^{0}} + \sum_{k^{0}}^{X} G_{qk^{0}}^{t}(")_{k^{0}q^{0}} g_{q^{0}R}^{t}(");$$
(6)

where the use has been made of the Fourier transform of the time-ordered G reen function  $G_{qk}^{t}(") = dte^{i"(t t^{0})}G_{qk}^{t}(t t^{0})$ ; and  $g_{kL}^{t}(")$ ,  $g_{q^{0}R}^{t}(")$  are the time-ordered G reen function of the left and right FM electrodes for the uncoupled system, respectively. By applying the Langreth theorem [9] to Eq.(5), we get

$$G_{kq}^{<}(") = \int_{q^{0}}^{X} \mathbb{F}_{qq^{0}}^{r}(") \int_{kq^{0}}^{y} g_{kL}^{<}(") + \mathbb{F}_{qq^{0}}^{<}(") \int_{kq^{0}}^{y} g_{kL}^{a}(")];$$
(7)

where the superscript r(a) denotes the retarded (advanced) "G reen function. The tunneling current becomes

$$I_{L}(V) = \frac{2e^{2}}{h} \frac{d''}{2} Re(\int_{k,qq^{0}}^{X} fTr(\int_{kq} F_{qq^{0}}^{r}('')) \int_{kq^{0}}^{Y} g_{kL}^{<}('') + F_{qq^{0}}^{<}('') \int_{kq^{0}}^{Y} g_{kL}^{a}('')])g):$$
(8)

To get useful analytical result we may assume for simplicity that the tunneling amplitude  $T_{kq}$  is independent of the momentum like the conventional consideration [1], but depends on spin. This suggests that apart from inclusion of the spin- ip scattering we have supposed that the tunneling amplitude of electrons for the spin-up channel di ers from that of the spin-down channel. As a result,  $T_{kq}$  becomes  $T = ( \begin{array}{c} T_1 & T_2 \\ T_3 & T_4 \end{array} )$ : In addition, the elements of T are assumed to be real. Up to the rst-order approximation to the G reen function  $F_{qq^0}^{t}$  ("), we get

$$I_{L}(V) = \frac{2e}{h}Re^{Z} \frac{d''}{2}[f('') f('' + eV)]Tr[T_{eff}('';V)];$$
(9)

where f (") is the Ferm i function,

$$T_{eff}(";V) = 2^{2}T R_{ID}(") R^{V} T^{V} D_{L}("+eV);$$
 (10)

and  $D_{L(R)}$  (") is a 2 2 diagonal matrix with two nonzero elements being the corresponding density of states (DOS) of electrons with spin up and down in the left (right) ferrom agnet. For a small bias voltage V; we obtain the tunneling conductance

$$G = \frac{2e^2}{h} T_{eff}; \qquad (11)$$

where  $T_{eff} = Tr [Re(T_{eff} ("_F; V = 0))]$ , and "<sub>F</sub> is the Ferm i energy. In comparison to the Landauer-Buttiker formula, one may nd that  $T_{eff}$  can be regarded as an elective tunneling transmission coelected which includes the contribution from spin-ip scatterings. Eq. (11) can be explicitly rewritten as

$$G = G_0 [1 + P_2 P_1^2 + P_3^2 \cos(f_f)];$$
(12)

where  $G_0 = \frac{e^2}{2h} [(T_1^2 + T_2^2)D_{L"} + (T_3^2 + T_4^2)D_{L\#}] (D_{R"} + D_{R\#}), P_1 = \frac{(T_1^2 T_2^2)D_{L"} (T_4^2 T_3^2)D_{L\#}}{(T_1^2 + T_2^2)D_{L"} + (T_3^2 + T_4^2)D_{L\#}};$  $P_2 = \frac{D_{R"} D_{R\#}}{D_{R"} + D_{R\#}}; P_3 = \frac{2(T_1T_2D_{L"} + T_3T_4D_{L\#})}{(T_1^2 + T_2^2)D_{L"} + (T_3^2 + T_4^2)D_{L\#}};$  tan  $f = \frac{P_3}{P_1}; D_{L"} = D_L (" + M_1 + eV); D_{L\#} = D_L (" + M_1 + eV); D_{L\#} = D_L (" + M_1 + eV); D_{R} = D_R (" + M_2); D_{R\#} = D_R (" M_2);$  and  $D_{L(R)}$  is the DOS of electrons in the left (right) ferrom agnet. One may observe that there is an angular shift induced by the spin- ip scatterings, as to be discussed below. Now let us bok at the angular dependence of the conductance G. When the spin- ip scattering is neglected, i.e.  $T_2 = T_3 = 0$ , and if we further assume  $T_1 = T_4$ , we recover the conventional expression for the conductance  $G = G_0 (1 + P_1P_2 \cos)$ ; which is familiar in literature [1,7], where  $G_0 = \frac{e^2}{2h}T_1^2 (D_{L^*} + D_{L^*}) (D_{R^*} + D_{R^*})$ , and  $P_1 = \frac{D_{L^*} D_{L^*}}{D_{L^*} + D_{L^*}}$  is the usual polarization of the left ferrom agnet, and  $P_3 = 0$ : When  $T_2 = T_3 = 0$  but  $T_1 \notin T_4$ , which in plies that even if the spin- ip scattering is ignored, but the tunneling am plitude of electrons for the spin-up channel is di erent from that for the spin-down channel, we can also get in this situation an expression

$$G = G_0^0 (1 + P_1^0 P_2 \cos );$$
 (13)

where  $G_0^0 = \frac{e^2}{2h} (T_1^2 D_{L^*} + T_4^2 D_{L^{\#}}) (D_{R^*} + D_{R^{\#}})$  and  $P_1^0 = \frac{T_1^2 D_{L^*} T_4^2 D_{L^{\#}}}{T_1^2 D_{L^*} + T_4^2 D_{L^{\#}}}$ : A though it looks seem ingly like the conventional form, it is clear that the di erence of the tunneling am plitudes for the two independent spin channels can still alter the magnitude of the conductance and the polarization as well.

On the other hand, the angular dependence of the tunnel conductance without considering the spin- ip e ects, as mentioned before, is well known:

$$G = G_{P} \cos^{2} \frac{1}{2} + G_{AP} \sin^{2} \frac{1}{2};$$
(14)

with  $G_P$  the conductance for parallel orientation of magnetizations in the two FM electrodes, and  $G_{AP}$  the conductance for the antiparallel orientation (see e.g. Refs. [1,6]). While in the present case, namely, with inclusion of the elect of spin-ip scatterings we not from Eq.(12) that the angular dependence of the conductance becomes

$$G = G_1 \cos^2 \frac{1}{2} + G_2 \sin^2 \frac{1}{2} + G_3 \sin ; \qquad (15)$$

where  $G_1 = \frac{e^2}{2h} fD_R \cdot [T_1^2 D_L \cdot + T_3^2 D_{L\#}] + D_R \cdot [T_2^2 D_L \cdot + T_4^2 D_L \cdot ]g$ ,  $G_2 = \frac{e^2}{2h} fD_R \cdot [T_2^2 D_L \cdot + T_4^2 D_L \cdot ]g$  $T_4^2 D_{L\#}] + D_{R\#}[T_1^2 D_{L"} + T_3^2 D_{L\#}]$ ; and  $G_3 = \frac{e^2}{2h} (D_{R"} D_{R\#}) (T_1 T_2 D_{L"} + T_3 T_4 D_{L\#})$ . One may see that apart from the conventional  $\cos^2 \frac{1}{2}$  and  $\sin^2 \frac{1}{2}$  terms there is an additional third term proportional to  $\sin$  . Here we should point out that  $G_1$  is the conductance in the case of the parallel alignment ( = 0) for the magnetizations of the two ferrom agnets, G  $_2$ is corresponding to the antiparallel case (=), and  $G_3$  gives an additional term for the noncollinear case ( $\neq$  0 and ), which disappears in the collinear cases. Certainly, these three coe cients G<sub>i</sub> (i = 1;2;3) contain the contributions from the spin- ip scatterings characterized by  $T_2$  and  $T_3$ . It is the e ect of spin- ip scatterings that enables the tunnel conductance not to be at the minimum when the magnetizations of the two ferrom agnets are antiparallel. This is understandable, because the spin- ip scattering process violates the spin conservation and can enable electrons in the spin-up band of one FM electrode tunneling through the insulator barrier into the spin-down band of another FM electrode, and vice versa, thereby giving rise to a phase shift, as shown in Eq.(12). It is emphasized that this shift will disappear when the e ect of spin-ip scattering is neglected. Therefore, Eqs. (12) and (15) can be view d as a generalization of the conventional expression for the tunnel conductance [see Eq.(14)]. It is interesting to note that the phenomenon of such an angular shift has been experimentally observed for a  $CoFe/A \downarrow 0_3/Co$  tunnel junction, as presented in Ref. [8] (see Fig.4 therein), where the maximum of the junction resistance appears at = 200, not 180, implying the angular shift  $_{\rm f}$  = 20. A lthough the authors of Ref. [8] did not mention the reasons why such an angular shift occurs in this FM -I-FM junction, in accordance with the aforem entioned analysis we may attribute this phenom enon possibly to the elect of the spin- ip scatterings. If this is acceptable, we can in turn infer the magnitude of the elect of spin- ip scatterings. To show it explicitly, let us assume T<sub>1</sub> T<sub>4</sub> and T<sub>2</sub> T<sub>3</sub> for simplicity, and de ne a parameter

$$= \frac{T_2}{T_1}; \tag{16}$$

which characterizes the magnitude of the e ect of spin- ip scatterings. The angular shift  $_{\rm f}$  versus the parameter is plotted in Fig. 1. It is seen that  $_{\rm f}$  is monotonously increasing with increasing :W hen approaches to 1,  $_{\rm f}$  = 90 which can be obtained from the expression of P<sub>1</sub> (see below). If > 1, then P<sub>1</sub> can be negative, leading to  $_{\rm f}$  larger than 90. To see more clearly the e ect of spin- ip scatterings on the conductance, we note that G<sub>0</sub> in Eq. (12) can be written as G<sub>0</sub> =  $(1 + {}^2)$ G<sub>0</sub>. In this case, P<sub>1</sub> =  $\frac{1}{1+{}^2}$ P<sub>1</sub>, and P<sub>3</sub> =  $\frac{2}{1+{}^2}$ . The -dependence of the conductance is presented in Fig. 2 (a). It can be seen that the conductance decreases with increasing when the magnetizations in the two ferrom agnets are parallel, while it increases for the antiparallel alignment. As > 1, one may observe that G ( = ) > G ( = 0), suggesting that the inverse TM R may occur. For the case of noncollinear alignments, with increasing the conductance rest increases rapidly and then decreases, and some peaks appear around 1.

We come to consider the e ect of spin- ip scatterings on the TMR. Recently, a number of experiments [4] for a few FM-I-FM tunnel junctions show that if the insulator thin Im is the material which diers from  $A l_2O_3$ ; such as SrT iO<sub>3</sub>,  $Ce_{0:69}La_{0:31}O_{1:845}$  and so on, the TMR, de ned as usual as 1 G (=)=G (=0); will be negative under certain conditions, which means G (=) > G (=0); exhibiting the so-called inverse TMR e ect. It is generally believed that this e ect may originate from the electronic states at the interface between a ferror agnetic layer and an insulating layer [4] which could give rise to the density of states in the minority spin band larger than that in the majority spin band at the Ferm i level. However, one may see below that the spin- ip scattering can also contribute to the inverse TMR. From (12) we nd that the TMR still has the apparently standard form

$$TM R = \frac{2P_1P_2}{1 + P_1P_2};$$
(17)

but  $P_1$ , de ned after Eq. (12) and containing the contribution from spin- ip scatterings, di ers from the conventional polarization  $P_1$ . In Ref. [3], M oodera et al calculated the TM R for the C oFe/A  $\frac{1}{2}O_3/C$  o junction according to the Julliere<sup>0</sup>s form u.a. The calculated result is 27%, while the experiment value is 24% at 4.2 K. If we adopt this experimental data, we can calculate the contribution of the spin- ip scatterings which is characterized by the parameter

. The obtained result for is about 0.28, where the spin polarization of electrons is taken as 47% for CoFe and 34% for Co  $\beta$ ]. It shows that the spin- ip scatterings m ight have a considerable e ect on the electrical transport of this tunnel junction. On the other hand, if we take the contribution from the spin- ip scatterings into account, then we can apply our form ula to estim ate the value of TMR, which could be closer to the experim ental result than using Julliere<sup>0</sup>s form ula. If the tunneling am plitudes satisfy a certain condition, P<sub>1</sub> can be negative, depending on the di erence between  $(T_1^2 - T_2^2)D_{L^*}$  and  $(T_4^2 - T_3^2)D_{L^{\#}}$ , resulting in that the TMR can be negative. The -dependence of the TMR is depicted in Fig. 2 (b). It can be seen that the TMR decreases with increasing , and becomes negative for > 1. This can be understood in the following. For 0 < < 1, the tunneling am plitude for the two independent channels  $(T_1)$  is larger than the tunneling am plitude for the spin- ip channel  $(T_2)$ . Owing to the spin- ip scatterings the polarization P<sub>1</sub> becomes e ective and small, leading to decreasing of the TMR.When > 1, i.e., the tunneling am plitude for the two independent channels is smaller than that for the spin- ip channel, the spin- ip scattering dom inates in the tunneling process, im plying that the electrons with spin up in the left FM electrode can tunnel through the insulator barrier to occupy the states of electrons with spin down in the right FM electrode via the spin- ip mechanism, thereby giving rise to contribution to the inverse TMR e ect.

The angular dependence of the TMR can be understood from the following de nition

$$TM R () = \frac{G () G (=)}{G (=0)} = \frac{P_2 (P_1 + \frac{q}{P_1^2 + P_3^2} \cos(\underline{f}))}{1 + P_1 P_2}$$
(18)

W hen = f, the TMR goes to its maximum which will be denoted by TMR (f) hereafter. In Fig. 3, the -dependence of the maximum TMR, i.e. TMR (f), is presented. A remarkable property is that TMR (f) has a peak at 0.82, which migh be a result of the spin- ip assisted tunneling. It is seen that TMR (f) approaches to a constant when increases to a large value. No matter how large is, TMR (f) is always positive.

The above discussion is based on the result up to the rst-order approximation for the G reen functions. To include contributions from higher-order G reen functions, it is better to consider them in a Keldysh space. We introduce the nonequilibrium G reen function in the Keldysh space as [9]

$$\mathfrak{G}_{qk}(\mathbf{t}; \mathbf{t}^{0}) = \begin{array}{c} \operatorname{G}_{qk}^{t}(\mathbf{t}; \mathbf{t}^{0}) \ \operatorname{G}_{kq}^{<}(\mathbf{t}; \mathbf{t}^{0}) \\ \operatorname{G}_{qk}^{>}(\mathbf{t}; \mathbf{t}^{0}) \ \operatorname{G}_{qk}^{e}(\mathbf{t}; \mathbf{t}^{0}) \end{array};$$
(19)

where  $G_{qk}^{t}$  (t; t<sup>0</sup>) is the time-ordered G reen function de ned as before,  $G_{kq}^{<(>)}$  (t; t<sup>0</sup>) is lesser (greater) G reen function, and  $G_{qk}^{e}$  (t; t<sup>0</sup>) is the antitim e-ordered G reen function. The elements of  $G_{qk}^{e}$  (t; t<sup>0</sup>) and  $G_{qk}^{>}$  (t; t<sup>0</sup>) are given by

$$G_{qk}^{0,p}(\mathbf{t}; \mathbf{t}^{0}) = \inf_{D} \mathbf{b}_{q} (\mathbf{t}) \mathbf{a}_{k}^{Y} \circ (\mathbf{t}^{0}) ]\mathbf{i}; \qquad (20)$$

$$G_{kq}^{0,p} (\mathbf{t}; \mathbf{t}^{0}) = \mathbf{i} \mathbf{b}_{q} (\mathbf{t}) \mathbf{a}_{k}^{Y} \circ (\mathbf{t}^{0}) :$$

A coording to Eqs. (5) and (6), we can make a sum of Feynman diagrams shown in Fig. 4. The result is

$$\hat{\mathbf{g}}_{kq}(\mathbf{"}) = \mathbf{g}_{R}(\mathbf{"})^{b}(\mathbf{"})\mathbf{g}_{L}(\mathbf{"});$$
 (21)

where  $i^{b}$  (") =  $i^{y}b_{3}$  ( $\mathfrak{P}$  b)  $^{1}$ , b =  $\mathfrak{g}_{L}$  (")  $b_{3}\mathfrak{g}_{R}$  (")  $^{y}b_{3}$ , = T R, and  $b_{3}$  is a Pauli matrix. From Eq. (2), the current can be rewritten as

$$I_{L}(V) = \frac{2e}{h}Re^{Z}\frac{d''}{2}Trf(\hat{g}_{qk}(''))_{12}g:$$
 (22)

A fter a tedious calculation, we get

$$I_{L}(V) = \frac{e}{h} R e^{Z} \frac{d''}{2} T r f F_{2}(b_{3} ib_{2}) F_{1} T_{eff}('';V) [(1 + T_{eff}('';V)=2)b_{0} + (f(''+eV) f(''))(b_{3}+ib_{2})T_{eff}('';V)]^{1} g; \qquad (23)$$

where T r denotes the trace over the spin space and the K eldysh space,  $b_0$  is the unit m atrix,  $b_i$  (i = 1;2;3) are Paulim atrices, and

$$\mathbf{P}_{1} = \begin{array}{ccc} 1 & 2f(\mathbf{"}) & 0 \\ 0 & 2f(\mathbf{"}) \end{array}; \mathbf{P}_{2} = \begin{array}{ccc} 2f(\mathbf{"} + eV) & 0 \\ 0 & 1 & 2f(\mathbf{"} + eV) \end{array};$$

Eq. (23) can be rewritten in a compact form

$$I_{L}(V) = \frac{4e}{h}Re^{Z}d''[f('' + eV) f('')]Trf[('';V) 1] ('';V)g;$$
(24)

where  $(";V) = \frac{T_{eff}(";V)}{2}$   $(1 + \frac{T_{eff}(";V)}{2})^{1}$  and  $T_{eff}(";V) = \frac{T_{eff}^{1}(";V)}{T_{eff}^{3}(";V)} \frac{T_{eff}^{2}(";V)}{T_{eff}^{4}(";V)}^{!}$  are

m atrices in spin space, and  $T_{eff}^{i}$  (i = 1;2;3;4) are the elements of the elective transmission m atrix  $T_{eff}$  (";V) given in Eq. (10). In principle, Eq. (24) gives the current including m ore corrections from the spin- ip scatterings, and the tunnel conductance can be obtained by  $G = @I_L$  (V)=@V. For a sm all bias voltage, we get

$$G = \frac{2e^2}{h} \Upsilon_{eff}, \qquad (25)$$

where  $T_{eff} = \frac{BT_{eff}^{0} + (T_{eff}^{1} ("_{F}) + T_{eff}^{4} ("_{F}))(2 + T_{eff}^{0})]}{P + T_{eff}^{0} + (T_{eff}^{1} ("_{F}) + T_{eff}^{4} ("_{F})))^{2}}$  with  $T_{eff}^{0} = 2 \ ^{4}D_{L"} ("_{F})D_{L\#} ("_{F})D_{R} ("_{F})D_{R\#} ("_{F}) (T_{1}T_{4} T_{2}T_{3})^{2}$ , can be viewed as the elective transm ission coecient. Compared to Eq. (11), Eq. (25) includes more corrections from the spin- ip scatterings. A lthough the angular dependence of G () determ ined by Eq. (25) boks more complex in form than one presented in Eq. (12), the behavior of G () versus is found to be qualitatively sim ilar to those shown in Fig. 2 (a) for a given .

In sum mary, we have investigated the e ect of spin- ip scatterings on the spin-dependent electrical transport in ferrom agnet-insulator-ferrom agnet tunnel junctions by using the nonequilibrium G meen function technique. When the e ect of the spin- ip scatterings is taken into account, the frequently used Julliere<sup>0</sup>s form ula for the tunnel conductance m ust be modiled, though the form looks seem ingly similar. It is found that the spin- ip scatterings could lead to an angular shift of the tunnel conductance, giving rise to the junction resistance not being the largest when the orientations of magnetizations in the two FM electrodes are antiparallel, which is quite consistent with the experimental observation in C oFe/A  $\frac{1}{2}O_3/C$  o tunnel junctions. A s the Julliere<sup>0</sup>s form ula overestim ates the value of the TM R, our derived form ula with inclusion of the e ect of spin- ip scatterings could estimate the TM R value closer to the experimental result, as discussed above. It is found that the spin- ip scattering could also lead to the inverse TM R e ect under certain conditions,

though it is not the only factor. The phenom enon of spin- ip assisted tunneling is clearly observed. W hen including high-order terms of the G reen function, the angular dependence of the tunnel conductance is qualitatively sim ilar, although the form looks m ore com plex. Finally, we would like to mention that our present derivation can be readily extended to other magnetic junctions.

#### ACKNOW LEDGMENTS

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Corresponding author. E-m ail: gsu@ gscas.ac.cn.

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FIGURE CAPTIONS

Fig. 1 The angular shift  $_{\rm f}$  versus the parameter , where the mass of single electron in both ferrom agnets are assumed as unity, the molecular elds in the two ferrom agnets are supposed to be the same and taken as 0:7eV ,  $"_{\rm F}$  = 1:5eV , and the coupling parameter  $T_1$  is chosen as 0:01 eV .

Fig. 2 The -dependence of the tunnel conductance (a) and the TMR (b), where the parameters are taken the same as those in Fig. 1.

Fig. 3 The -dependence of the maximum tunnel magnetoresistance TM R (  $_{\rm f}$ ), where the parameters are taken the same as those in Fig. 1.

Fig. 4 Feynm an diagram s for the G reen function §  $_{\rm qk}$  (").

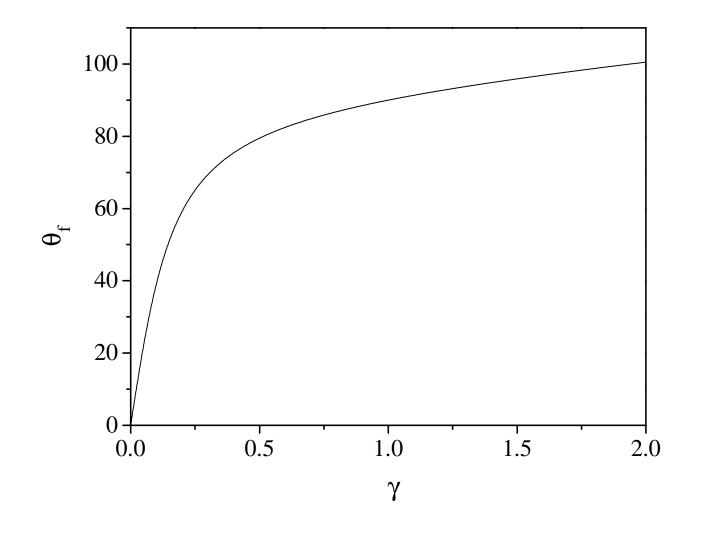


Fig.1 Zhu et al

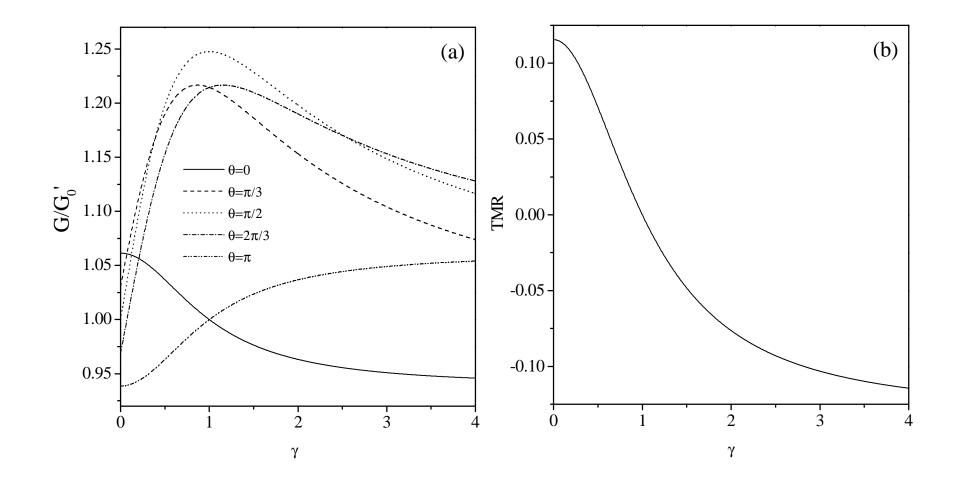


Fig.2 Zhu et al

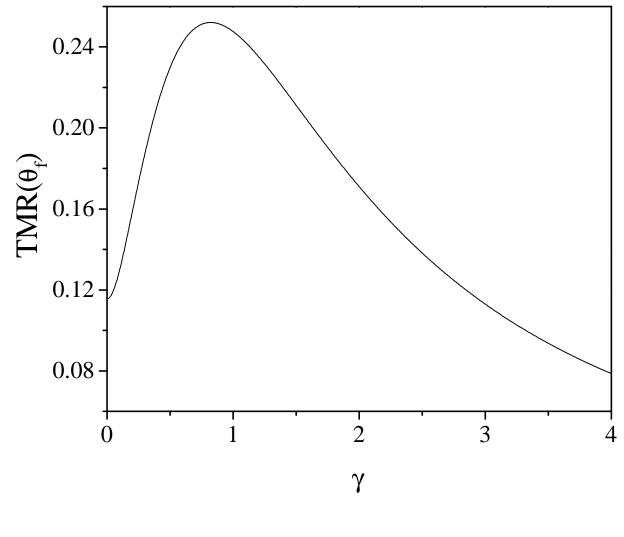
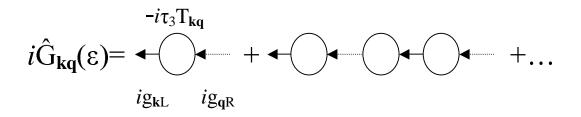


Fig.3 Zhu et al



# Fig.4 Zhu et al